

Product Change Notification

Product Group: OPT/Tue Aug 6, 2024/PCN-OPT-1324-2024-REV-0



VEMT37..X02: change of the Phototransistor chip

For further information, please contact your regional Vishay office.

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-	-	-

Description of Change: Change of the phototransistor chip from T4530P to T5096P

The Phototransistors are now manufactured on 6 inch wafers instead of

the 4 inch wafers

Apart from that, change of the phototransistor results in minor changes in

device characteristics, changes in

the datasheet characteristics are listed in the document attached to this

PCN: Changelog

Reason for Change: To qualify new chip T5096P on 6" wafer

Expected Influence on Quality/Reliability/Performance: No influence on quality, reliability and performance expected.

Nevertheless, we recommend to test the product in customers application

Part Numbers/Series/Families Affected: Please see materials list on the succeeding page.

Vishay Brand(S): Vishay Semiconductors

Time Schedule:

Start Shipment Date: Thu Feb 6, 2025

Sample Availability: available upon request

Product Identification: VEMT3705FX02, VEMT3705X02, VEMT3705F, VEMT3705

Qualification Data: available upon request

This PCN is considered approved, without further notification, unless we receive specific customer concerns before Thu Sep 5, 2024 or as specified by contract.

Issued By: Elena Poklonskaya, elena.poklonskaya@vishay.com



Product Change Notification

n (PCN)

Product Group: OPT/Tue Aug 6, 2024/PCN-OPT-1324-2024-REV-0

VEMT3700FX01-GS08	VEMT3700FX01-GS18	VEMT3700X01-GS08	VEMT3700X01-GS18	VEMT3700-GS08
VEMT3700-GS18	VEMT3700F-GS08	VEMT3700F-GS18		



VEMT3705X02 - Datasheet

Rev 1.0, 29-Jul-2024 Based on VEMT3700 Rev 1.6, 14-Jul-2010



VEMT3705X02 - Datasheet

VEMT3700 Rev. 1.6

FEATURES

- · Package type: surface mount
- Package form: PLCC-2
- Dimensions (L x W x H in mm): 3.5 x 2.8 x 1.75
- · High photo sensitivity
- · High radiant sensitivity
- Suitable for visible and near infrared radiation
- · Fast response times
- Angle of half sensitivity: $\phi = \pm 60^{\circ}$
- · Package notch indicates collector
- · Package matched with IR emitter series VSML3710
- Floor life: 168 h, MSL 3, acc. J-STD-020
- · Lead (Pb)-free reflow soldering
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

RoHS

GREEN

VEMT3705X02 Rev 1.0

FEATURES

- · Package type: surface-mount
- Package form: PLCC-2
- Dimensions (L x W x H in mm): 3.5 x 2.8 x 1.75

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- Fast response times
- · Suitable for visible and near infrared radiation
- Angle of half sensitivity: $\phi = \pm 60^{\circ}$
- · Package notch indicates collector
- Package matched with IR emitter series VSML3710
- Floor life: 168 h, MSL 3, according to J-STD-020
- · Lead (Pb)-free reflow soldering
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912







VEMT3705X02 - Datasheet

VEMT3700 Rev. 1.6

VEMT3705X02 Rev 1.0

PRODUCT SUMMARY			
COMPONENT	I _{ce} (mA)	φ (deg)	λ _{0.4} (nm)
VEMT3700	0.5	± 60	450 to 1080
		•	

PRODUCT SUMMARY			
COMPONENT	I _{ca} (mA)	φ (°)	λ _{0.1} (nm)
VEMT3705X02	0.6	± 60	480 to 1050

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VEMT3705X02 - Datasheet

VEMT3700 Rev. 1.6

VEMT3705X02 Rev 1.0

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Collector emitter voltage		Vceo	70	V
Emitter collector voltage		V _{ECO}	5	V
Collector current		Ic	50	mA
Collector peak current	$t_p/T \le 0.1, t_p \le 10 \ \mu s$	Ісм	100	mA
Power dissipation		Pv	100	mW
Junction temperature		T _i	100	°C
Operating temperature range		T _{amb}	- 40 to + 100	°C
Storage temperature range		T _{stq}	- 40 to + 100	°C
Soldering temperature	Acc. reflow solder profile fig. 10	T _{sd}	260	°C
Thermal resistance junction/ambient	Soldered on PCB with pad dimensions: 4 mm x 4 mm	RthJA	400	K/W

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Collector emitter voltage		V _{CEO}	20	V
Emitter collector voltage		V _{ECO}	7.8	V
Collector current		lc	50	mA
Collector peak current	$t_p/T \le 0.1, t_p \le 10 \ \mu s$	I _{CM}	100	mA
Power dissipation		P _V	100	mW
Junction temperature		T	100	°C
Temperature range		T _{amb}	-40 to +100	°C
Storage temperature range		T _{stg}	-40 to +100	°C
Soldering temperature	According to reflow solder profile Fig. 10	T _{sd}	260	°C
Thermal resistance junction to ambient	Soldered on PCB with pad dimensions: 4 mm v 4 mm	B	400	KΛN

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VEMT3705X02 - Datasheet

VEMT3700 Rev. 1.6

VEMT3705X02 Rev 1.0

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	I _C = 1 mA	V _{(BR)CEO}	70			V
Collector emitter dark current	V _{CE} = 20 V, E = 0	ICEO		1	200	nA
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz, E = 0	C _{CEO}		3		pF
Collector ligth current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_{CE} = 5 \text{ V}$	Ica	0.25	0.5		mA
Angle of half sensitivity		φ		± 60		deg
Wavelength of peak sensitivity		λρ		850		nm
Range of spectral bandwidth		λ _{0.1}		450 to 1080		nm
Collector emitter saturation voltage	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$, $I_C = 0.1 \text{ mA}$	VCEsat		0.15	0.3	V
Rise time, fall time	$V_S = 5$ V, $I_C = 1$ mA, $\lambda = 950$ nm, $R_L = 1$ k Ω	t _r /t _f		6		μs
nise time, tall time	$V_S = 5 \text{ V}, I_C = 1 \text{ mA}, \lambda = 950 \text{ nm},$ $R_L = 100 \Omega$	t _r /t _f		2		μs
Cut-off frequency	$V_S = 5 \text{ V. } I_C = 2 \text{ mA}, R_I = 100 \Omega$	f _c		180		kHz

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	I _C = 1 mA	V _{(BR)CEO}	20	-	-	V
Collector emitter dark current	V _{CE} = 20 V, E = 0	ICEO	-	0.2	200	nA
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz, E = 0	C _{CEO}	-	5	-	pF
Collector light current	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 940 \text{ nm}$, $V_{CE} = 5 \text{ V}$	I _{ca}	0.25	0.6		mA
Angle of half sensitivity		φ	-	± 60	-	۰
Wavelength of peak sensitivity		λp	-	950	-	nm
Range of spectral bandwidth		λ _{0.1}		480 to 1050	-	nm
Collector emitter saturation voltage	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 940 \text{ nm}$, $I_C = 0.1 \text{ mA}$	V _{CEsat}	100	0.11	0.3	٧
Rise time	$V_{CE} = 5 \text{ V}, I_{C} = 0.7 \text{ mA},$ $\lambda = 940 \text{ nm}, R_{L} = 100 \Omega$	t _r	-	14	-	μs
Fall time	$V_{CE} = 5 \text{ V}, I_{C} = 0.7 \text{ mA},$ $\lambda = 940 \text{ nm}, R_{I} = 100 \Omega$	t _f	-	21	(*)	μs

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VEMT3705X02 - Datasheet

VEMT3700 Rev. 1.6

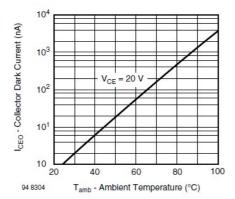


Fig. 2 - Collector Dark Current vs. Ambient Temperature

VEMT3705X02 Rev 1.0

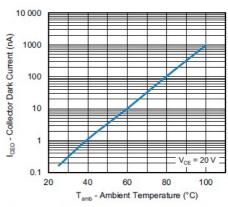


Fig. 2 - Collector Dark Current vs. Ambient Temperature

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VEMT3705X02 - Datasheet

VEMT3700 Rev. 1.6

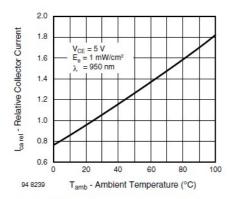


Fig. 3 - Relative Collector Current vs. Ambient Temperature

VEMT3705X02 Rev 1.0

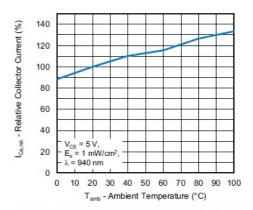


Fig. 3 - Relative Collector Current vs. Ambient Temperature

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VEMT3700 Rev. 1.6

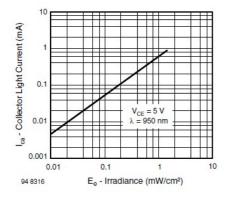


Fig. 4 - Collector Light Current vs. Irradiance

VEMT3705X02 Rev 1.0

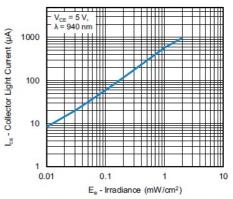


Fig. 4 - Collector Light Current vs. Irradiance

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VEMT3705X02 - Datasheet

VEMT3700 Rev. 1.6

Lca - Collector Light Current (mA) $\lambda = 950 \text{ nm}$ 0.2 mW/cm V_{CE} - Collector Emitter Voltage (V)

Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

VEMT3705X02 Rev 1.0

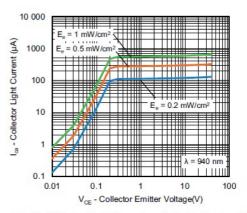


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

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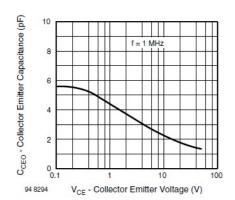


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage

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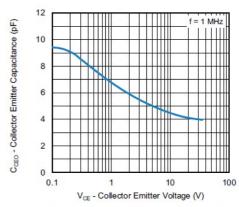


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage



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VEMT3705X02 - Datasheet

VEMT3700 Rev. 1.6

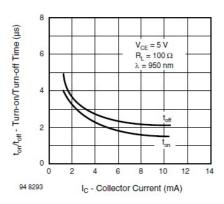


Fig. 7 - Turn-on/Turn-off Time vs. Collector Current

VEMT3705X02 Rev 1.0

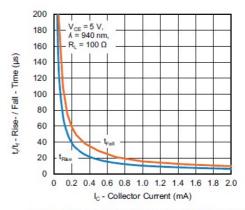


Fig. 7 - Turn-on / Turn-off Time vs. Collector Current

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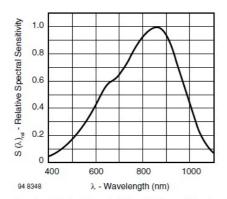


Fig. 8 - Relative Spectral Sensitivity vs. Wavelength

VEMT3705X02 Rev 1.0

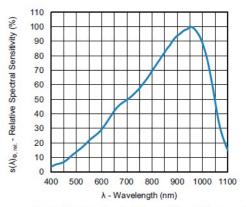


Fig. 8 - Relative Spectral Sensitivity vs. Wavelength

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VEMT3705X02 - Datasheet

VEMT3700 Rev. 1.6

0° 10° 20° 30° 40° 8 10° 20° 30° 40° 8 10° 40° 40° 8 10° 40° 8 10° 40° 8 10° 40° 8 10° 40° 8 10° 40° 8 10° 40° 40° 8 10° 8 10°

Fig. 9 - Relative Radiant Sensitivity vs. Angular Displacement

VEMT3705X02 Rev 1.0

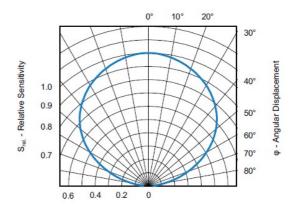


Fig. 9 - Relative Sensitivity vs. Angular Displacement

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VEMT3705FX02 - Datasheet

Rev 1.0, 06-Aug-2024 Based on VEMT3700F Rev 1.6, 14-Jul-2010



VEMT3705X02 - Datasheet

VEMT3700F Rev. 1.6

VEMT3705FX02 Rev 1.0

FEATURES

- · Package type: surface mount
- Package form: PLCC-2
- Dimensions (L x W x H in mm): 3.5 x 2.8 x 1.75
- · High radiant sensitivity
- · Fast response times
- Daylight blocking filter matched with 870 nm to 950 nm emitters
- Angle of half sensitivity: φ = ± 60°
- · Package notch indicates collector
- Package matched with IR emitter series VSML3710
- Floor life: 168 h, MSL 3, acc. J-STD-020
- · Lead (Pb)-free reflow soldering
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

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FEATURES

- · Package type: surface-mount
- · Package form: PLCC-2
- Dimensions (L x W x H in mm): 3.5 x 2.8 x 1.75

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- Fast response times
- · Daylight blocking filter matched with 870 nm to 950 nm emitters
- Angle of half sensitivity: φ = ± 60°
- · Package notch indicates collector
- Package matched with IR emitter series VSMI 3710
- . Floor life: 168 h, MSL 3, according to J-STD-020
- · Lead (Pb)-free reflow soldering
- · Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





VEMT3705X02 - Datasheet

VEMT3700F Rev. 1.6

VEMT3705FX02 Rev 1.0

PRODUCT SUMMARY			
COMPONENT	I _{ca} (mA)	φ (deg)	λ _{0.5} (nm)
VEMT3700F	0.5	± 60	870 to 1050

OMPONENT	I _{ca} (mA)	φ (°)	λ _{0.5} (nm)
/EMT3705FX02	0.5	± 60	880 to 1050

Test conditions see table "Basic Characteristics"

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VEMT3705X02 - Datasheet

VEMT3700F Rev. 1.6

VEMT3705FX02 Rev 1.0

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Collector emitter voltage		V _{CEO}	70	٧
Emitter collector voltage		V _{ECO}	5	V
Collector current		Ic	50	mA
Collector peak current	t _p /T ≤ 0.1, t _p ≤ 10 μs	I _{CM}	100	mA
Power dissipation		Pv	100	mW
Junction temperature		Tj	100	°C
Operating temperature range		T _{amb}	- 40 to + 100	°C
Storage temperature range		T _{stg}	- 40 to + 100	°C
Soldering temperature	Acc. reflow solder profile fig. 10	T _{sd}	260	°C
Thermal resistance junction/ambient	Soldered on PCB with pad dimensions: 4 mm x 4 mm	RthJA	400	K/W

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Collector emitter voltage		V _{CEO}	20	V
Emitter collector voltage		V _{ECO}	7.8	V
Collector current		Ic	50	mA
Collector peak current	$t_p/T \le 0.1, t_p \le 10 \ \mu s$	I _{CM}	100	mA
Power dissipation		Pv	100	mW
Junction temperature		Ti	100	°C
Temperature range		Tamb	-40 to +100	°C
Storage temperature range		T _{stg}	-40 to +100	°C
Soldering temperature	According to reflow solder profile Fig. 10	T _{sd}	260	°C
Thermal resistance junction to ambient	Soldered on PCB with pad dimensions: 4 mm x 4 mm	R _{thJA}	400	K/W



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VEMT3705X02 - Datasheet

VEMT3700F Rev. 1.6

VEMT3705FX02 Rev 1.0

BASIC CHARACTERISTICS (T _{amb} = 25 °C, unless otherwise specified)									
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT			
Collector emitter breakdown voltage	I _C = 1 mA	V _{(BR)CEO}	70			V			
Collector emitter dark current	V _{CE} = 20 V, E = 0	ICEO		1	200	nA			
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz, E = 0	C _{CEO}		3		pF			
Collector ligth current	$E_e = 1 \text{ mW/cm}^2, \lambda = 950 \text{ nm}, V_{CE} = 5 \text{ V}$	Ica	0.25	0.5		mA			
Angle of half sensitivity		φ		± 60		deg			
Wavelength of peak sensitivity		λρ		940		nm			
Range of spectral bandwidth		λο.5		870 to 1050		nm			
Collector emitter saturation voltage	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$, $I_C = 0.1 \text{ mA}$	V _{CEsat}		0.15	0.3	٧			
Rise time, fall time	$V_S = 5 \text{ V, } I_C = 1 \text{ mA, } \lambda = 950 \text{ nm,} \\ R_L = 1 \text{ k}\Omega$	t _e /t _f		6		μs			
	$V_S = 5 \text{ V}, I_C = 1 \text{ mA}, \lambda = 950 \text{ nm},$ $R_L = 100 \Omega$	t _r /t _f		2		μs			
Cut-off frequency	$V_S = 5 \text{ V}, I_C = 2 \text{ mA}, R_L = 100 \Omega$	f _c		180		kHz			

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Collector emitter breakdown voltage	I _C = 1 mA	V _{(BR)CEO}	20	-	-	V
Collector emitter dark current	V _{CE} = 20 V, E = 0	I _{CEO}	-	0.2	200	nA
Collector emitter capacitance	V _{CE} = 5 V, f = 1 MHz, E = 0	C _{CEO}	-	5	-	pF
Collector light current	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 940 \text{ nm}$, $V_{CE} = 5 \text{ V}$	Ica	0.25	0.6	-	mA
Angle of half sensitivity		φ	- 2	± 60	-	0
Wavelength of peak sensitivity	1	λp		950		nm
Range of spectral bandwidth	1	λ _{0.1}	-	480 to 1050	-	nm
Collector emitter saturation voltage	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 940 \text{ nm}$, $I_C = 0.1 \text{ mA}$	V _{CEsat}	-	0.11	0.3	٧
Rise time	$V_{CE} = 5 \text{ V}, I_{C} = 0.7 \text{ mA},$ $\lambda = 940 \text{ nm}, R_{L} = 100 \Omega$	t,	-	14	-	μs
Fall time	$V_{CE} = 5 \text{ V}, I_{C} = 0.7 \text{ mA},$ $\lambda = 940 \text{ nm}, R_{I} = 100 \Omega$	t _f	-	21	-	μs

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VEMT3705X02 - Datasheet

VEMT3700F Rev. 1.6

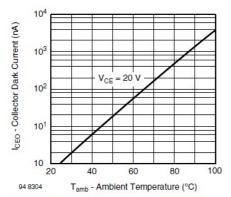


Fig. 2 - Collector Dark Current vs. Ambient Temperature

VEMT3705FX02 Rev 1.0

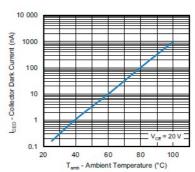


Fig. 2 - Collector Dark Current vs. Ambient Temperature

VEMT3705X02 - Datasheet

VEMT3700F Rev. 1.6

VEMT3705FX02 Rev 1.0

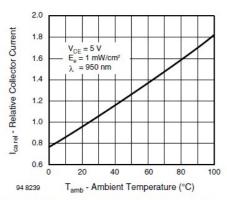


Fig. 3 - Relative Collector Current vs. Ambient Temperature

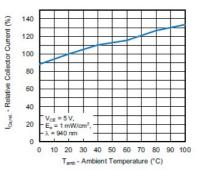


Fig. 3 - Relative Collector Current vs. Ambient Temperature

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VEMT3705X02 - Datasheet

VEMT3700F Rev. 1.6

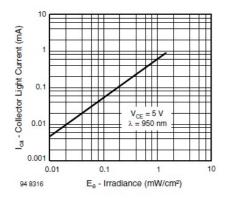


Fig. 4 - Collector Light Current vs. Irradiance

VEMT3705FX02 Rev 1.0

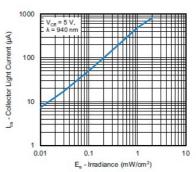


Fig. 4 - Collector Light Current vs. Irradiance



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VEMT3705X02 - Datasheet

VEMT3700F Rev. 1.6

VEMT3705FX02 Rev 1.0

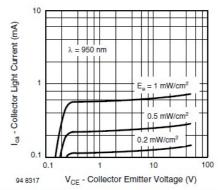


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

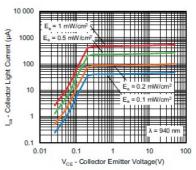


Fig. 5 - Collector Light Current vs. Collector Emitter Voltage

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VEMT3705X02 - Datasheet

VEMT3700F Rev. 1.6

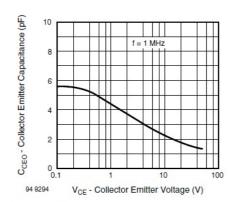


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage

VEMT3705FX02 Rev 1.0

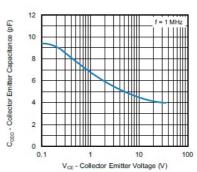


Fig. 6 - Collector Emitter Capacitance vs. Collector Emitter Voltage



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VEMT3705X02 - Datasheet

VEMT3700F Rev. 1.6

VEMT3705FX02 Rev 1.0

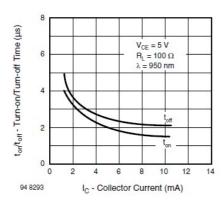


Fig. 7 - Turn-on/Turn-off Time vs. Collector Current

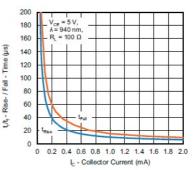


Fig. 7 - Turn-on / Turn-off Time vs. Collector Current

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VEMT3705X02 - Datasheet

VEMT3700F Rev. 1.6

S (\(\cdot)\)_{rel} - Relative Spectral Sensitivity 1.0 0.8 0.6 0.2 950 1050 1150 λ - Wavelength (nm)

Fig. 8 - Relative Spectral Sensitivity vs. Wavelength

VEMT3705FX02 Rev 1.0

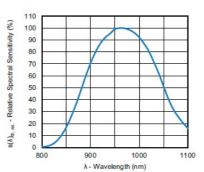


Fig. 8 - Relative Spectral Sensitivity vs. Wavelength



VEMT3705X02 - Datasheet

VEMT3700F Rev. 1.6

VEMT3705FX02 Rev 1.0

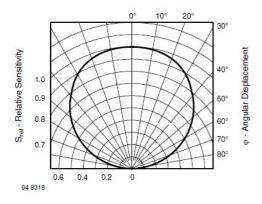


Fig. 9 - Relative Radiant Sensitivity vs. Angular Displacement

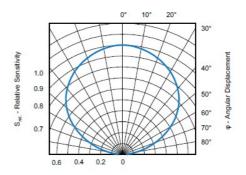


Fig. 9 - Relative Sensitivity vs. Angular Displacement

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THANK YOU